



UNISONIC TECHNOLOGIES CO., LTD

2N60L

Power MOSFET

2 Amps, 600/650 Volts
N-CHANNEL MOSFET

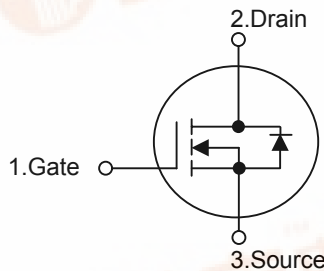
DESCRIPTION

The UTC **2N60L** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} = 5\Omega @ V_{GS} = 10V$
- * Ultra Low gate charge (typical 9.0nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 5.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL

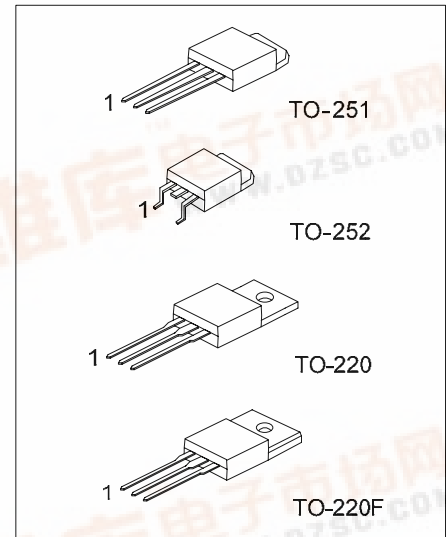


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2N60L-x-TA3-T	2N60LL-x-TA3-T	TO-220	G	D	S	Tube
2N60L-x-TF3-T	2N60LL-x-TF3-T	TO-220F	G	D	S	Tube
2N60L-x-TM3-T	2N60LL-x-TM3-T	TO-251	G	D	S	Tube
2N60L-x-TN3-R	2N60LL-x-TN3-R	TO-252	G	D	S	Tape Reel
2N60L-x-TN3-T	2N60LL-x-TN3-T	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

		(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TM3: TO-251, TN3: TO-252 (3) A: 600V, B: 650V (4) L: Lead Free Plating, Blank: Pb/Sn
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*Pb-free plating product number: 2N60LL

2N60L

Power MOSFET

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage	2N60L-A	V_{DS}	600	V
	2N60L-B		650	V
Gate-Source Voltage		V_{GS}	± 30	V
Avalanche Current (Note 1)		I_{AR}	2.0	A
Drain Current Continuous	$T_C = 25^\circ\text{C}$	I_D	2.0	A
	$T_C = 100^\circ\text{C}$		1.26	A
Drain Current Pulsed (Note 1)		I_{DP}	8.0	A
Avalanche Energy	Single Pulsed (Note 2)	E_{AS}	140	mJ
	Repetitive (Note 1)	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Total Power Dissipation	TO-220	P_D	32	W
	TO-220F		9	W
	TO-251		25	W
	TO-252		20	W
Junction Temperature		T_J	+150	
Operating Temperature		T_{OPR}	-55 ~ +150	
Storage Temperature		T_{STG}	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction-Ambient	TO-251	θ_{JA}	65	/W
	TO-252		58	
	TO-220		43	
	TO-220F		38	
Thermal Resistance Junction-Case	TO-251	θ_{JC}	5	
	TO-252		6	
	TO-220		4	
	TO-220F		12	

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	2N60L-A	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600		V
	2N60L-B			650		V
Drain-Source Leakage Current		I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$		10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS} = 30V, V_{DS} = 0V$		100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$		-100	nA
Breakdown Voltage Temperature Coefficient	BV_{DSS}/T_J	$I_D = 250\mu A$, Referenced to 25°C		0.4		V/
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$		3.8	5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		270	350	pF
Output Capacitance	C_{OSS}			40	50	pF
Reverse Transfer Capacitance	C_{RSS}			5	7	pF

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D (ON)}	V _{DD} =300V, I _D =2.4A, R _G =25Ω (Note 4, 5)		10	30	ns
Turn-On Rise Time	t _R			25	60	ns
Turn-Off Delay Time	t _{D (OFF)}			20	50	ns
Turn-Off Fall Time	t _F			25	60	ns
Total Gate Charge	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =2.4A (Note 4, 5)		9.0	11	nC
Gate-Source Charge	Q _{GS}			1.6		nC
Gate-Drain Charge	Q _{GD}			4.3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _{SD} = 2.0 A			1.4	V
Continuous Drain-Source Current	I _{SD}				2.0	A
Pulsed Drain-Source Current	I _{SM}				8.0	A
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _{SD} = 2.4A, di/dt = 100 A/μs (Note4)		180		ns
Reverse Recovery Charge	Q _{RR}			0.72		μC

Note: 1. Repetitive Rating : Pulse width limited by T_J
2. $L=64mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J = 25^\circ C$
3. $I_{SD} \leq 2.4A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ C$
4. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

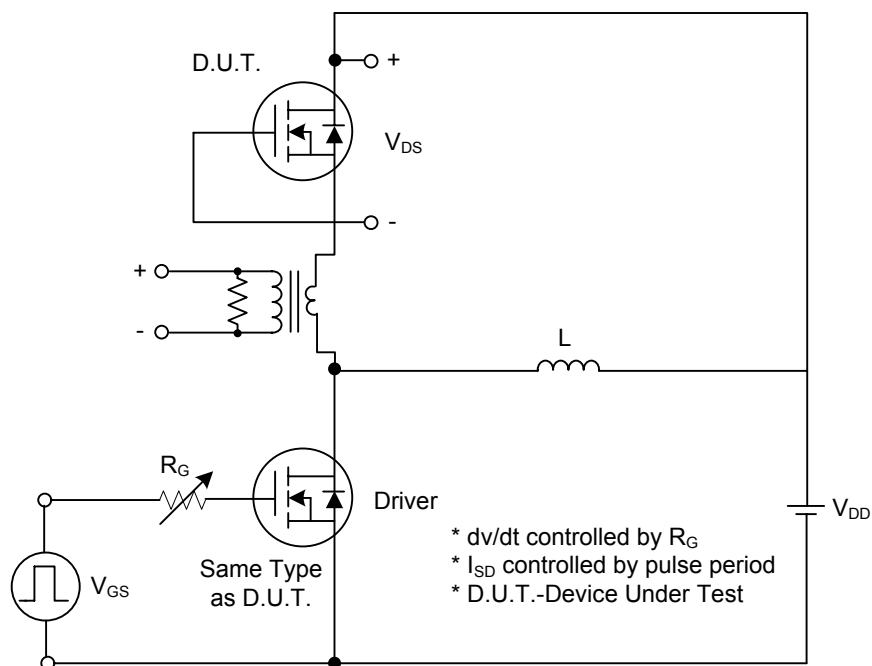


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

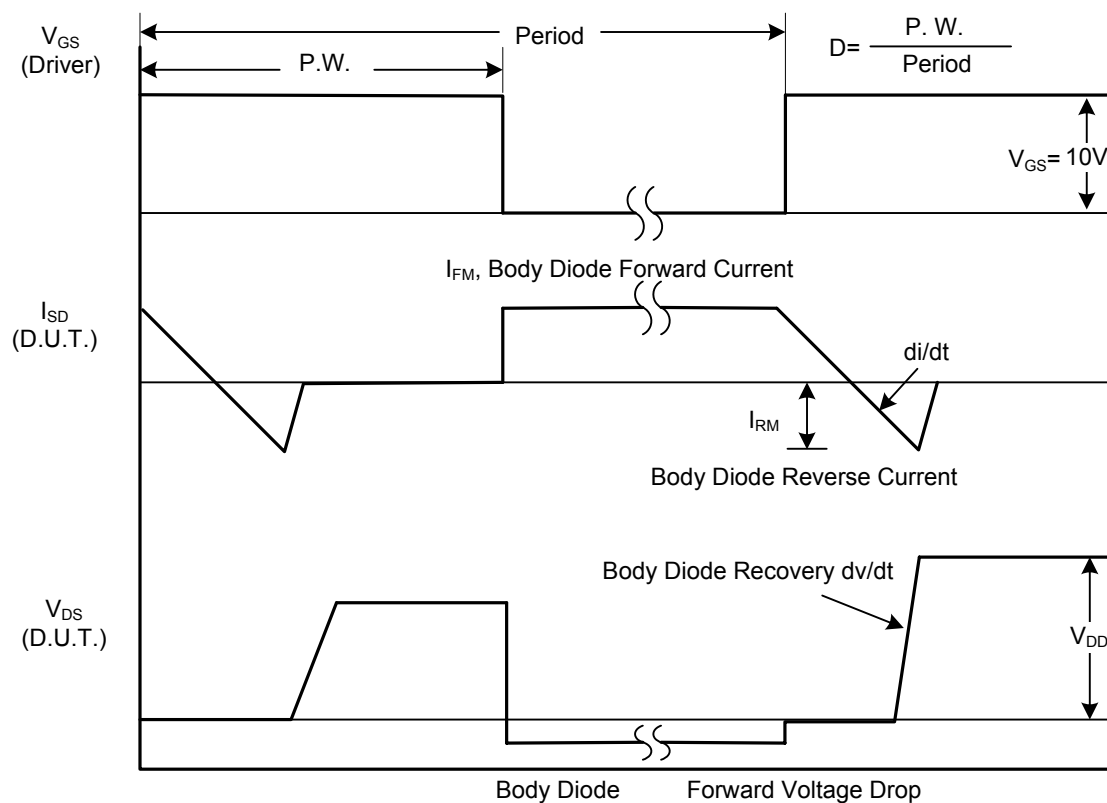


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

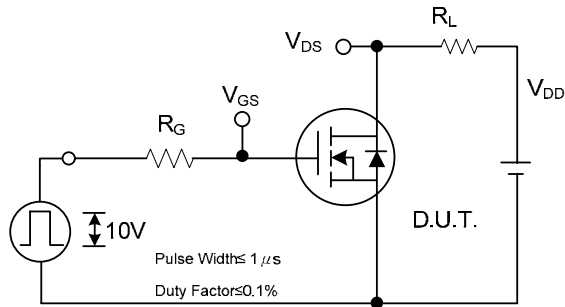


Fig. 2A Switching Test Circuit

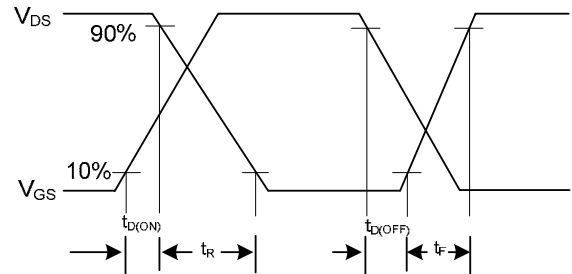


Fig. 2B Switching Waveforms

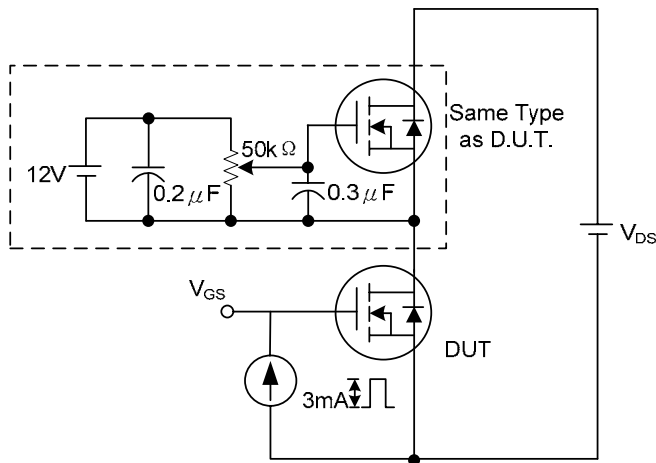


Fig. 3A Gate Charge Test Circuit

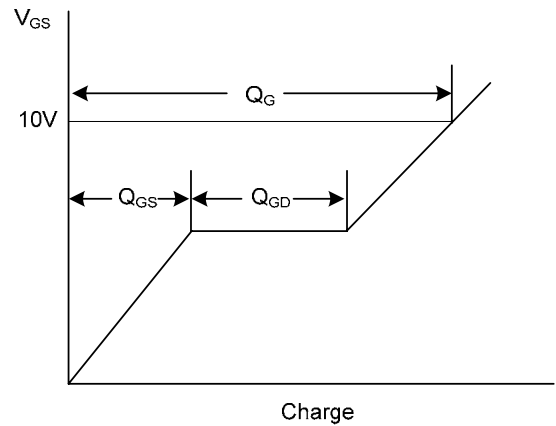


Fig. 3B Gate Charge Waveform

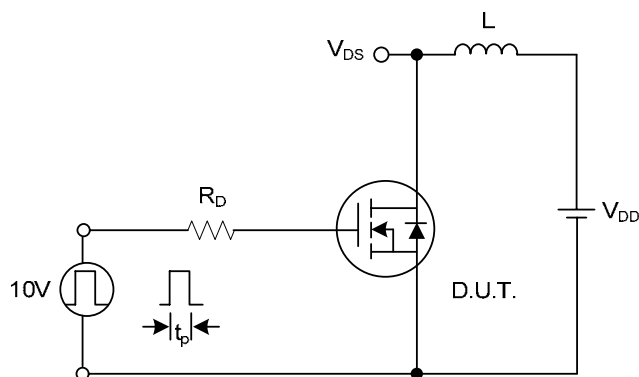


Fig. 4A Unclamped Inductive Switching Test Circuit

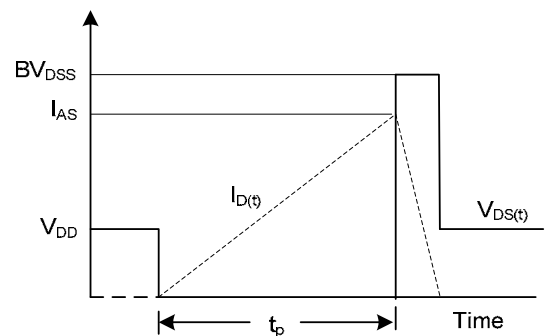
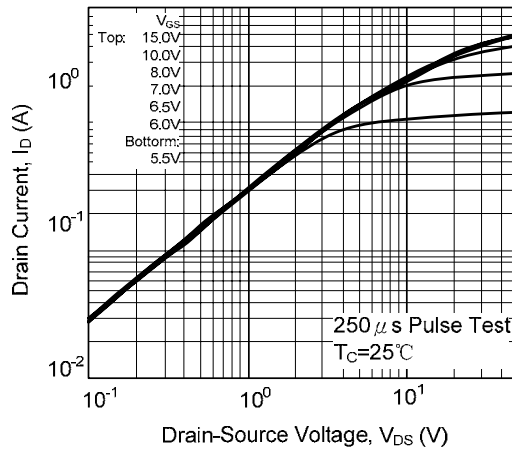


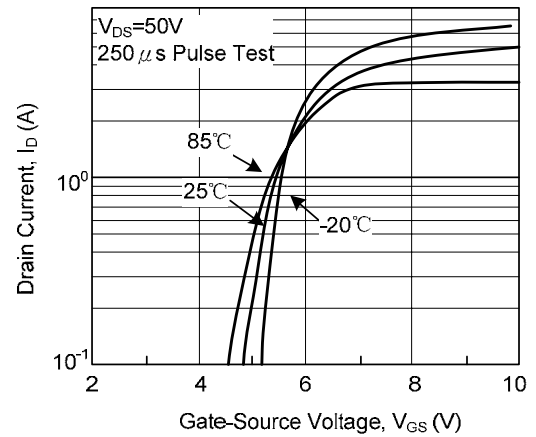
Fig. 4B Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

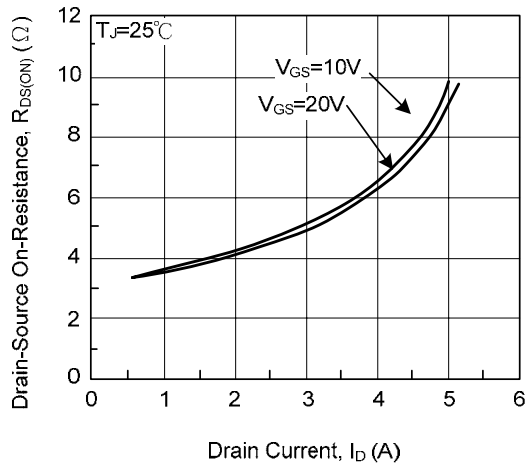
On-Region Characteristics



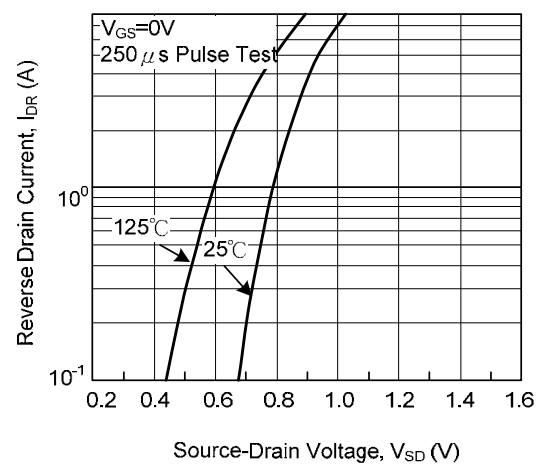
Transfer Characteristics



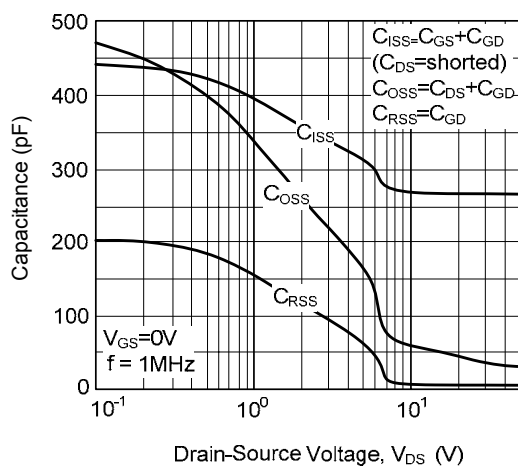
On-Resistance Variation vs. Drain Current and Gate Voltage



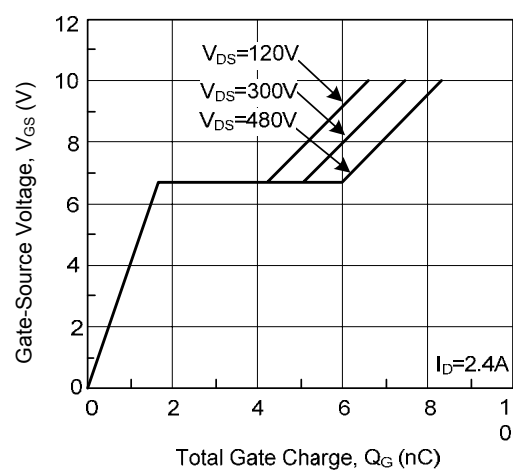
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance vs. Drain-Source Voltage

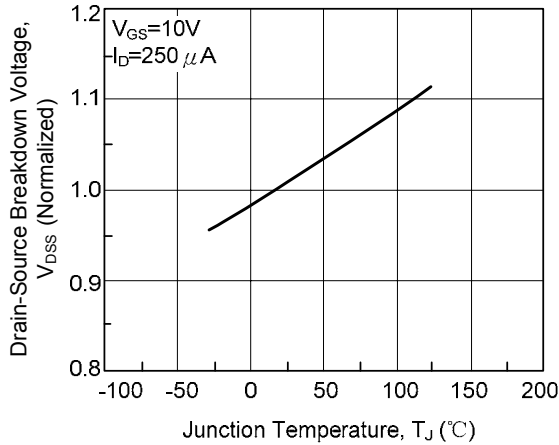


Gate Charge vs. Gate Charge Voltage

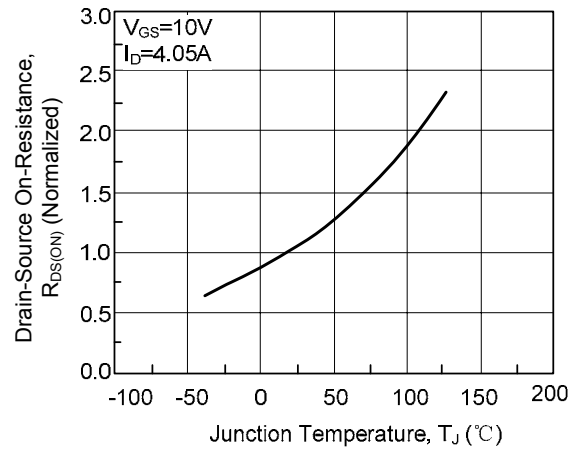


■ TYPICAL CHARACTERISTICS(Cont.)

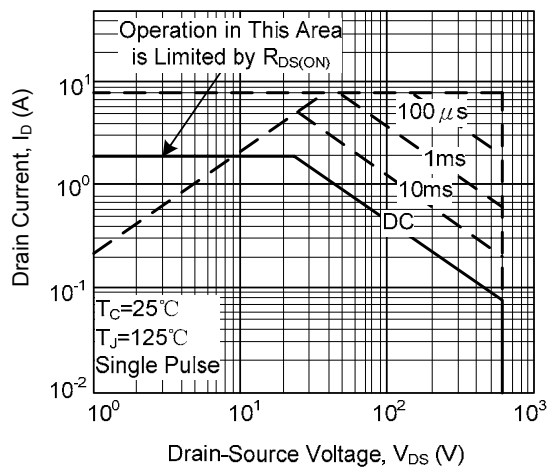
Breakdown Voltage vs. Temperature



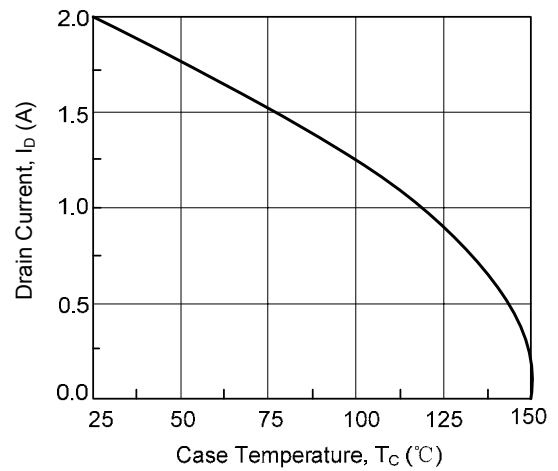
On-Resistance vs. Temperature



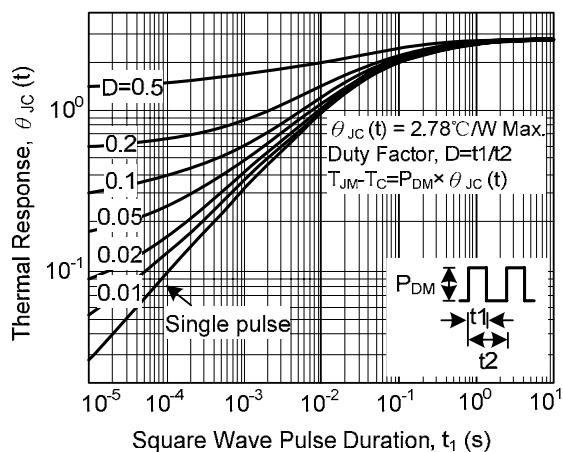
Max. Safe Operating Area



Max. Drain Current vs. Case Temperature



Thermal Response



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